

CY62256VN

256-Kbit (32 K × 8) Static RAM

Features

- Temperature ranges □ Commercial: 0 °C to +70 °C □ Industrial: -40 °C to +85 °C □ Automotive-A: -40 °C to +85 °C □ Automotive-E: -40 °C to +125 °C
- Speed: 70 ns
- Low voltage range: 2.7 V to 3.6 V
- Low active power and standby power
- Easy memory expansion with CE and OE features
- TTL compatible inputs and outputs
- Automatic power-down when deselected
- CMOS for optimum speed and power
- Available in standard Pb-free and non Pb-free 28-pin (300-mil) narrow SOIC, 28-pin TSOP-I, and 28-pin reverse TSOP-I packages

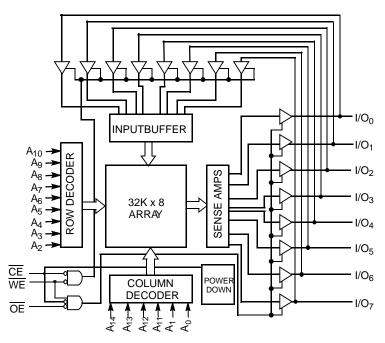
Logic Block Diagram

Functional Description

The CY62256VN family is composed of two high performance CMOS static RAM's organized as 32K words by 8 bits. Easy memory expansion is provided by an active LOW chip enable (\overline{CE}) and active LOW output enable (\overline{OE}) and tristate drivers. These devices have an automatic power-down feature, reducing the power consumption by over 99% when deselected.

An active LOW write enable signal ($\overline{\text{WE}}$) controls the writing/reading operation of the memory. When $\overline{\text{CE}}$ and $\overline{\text{WE}}$ inputs are both LOW, data on the eight data input/output pins (I/O_0 through I/O_7) is written into the memory location addressed by the address present on the address pins (A_0 through A_{14}). Reading the device is accomplished by selecting the device and enabling the outputs, $\overline{\text{CE}}$ and $\overline{\text{OE}}$ active LOW, while $\overline{\text{WE}}$ remains inactive or HIGH. Under these conditions, the contents of the location addressed by the information on address pins are present on the eight data input/output pins.

The input/output pins remain in a high impedance state unless the chip is selected, outputs are enabled, and write enable (WE) is HIGH.



198 Champion Court



CY62256VN

Contents

Product Portfolio	3
Pin Configurations	3
Pin Definitions	3
Maximum Ratings	4
Operating Range	
Electrical Characteristics	
Capacitance	
Thermal Resistance	
AC Test Loads and Waveforms	
Data Retention Characteristics	
Data Retention Waveform	
Switching Characteristics	
Switching Waveforms	
Typical DC and AC Characteristics	
Truth Table	

Ordering Information	12
Ordering Code Definitions	12
Package Diagrams	13
Acronyms	15
Document Conventions	15
Units of Measure	15
Document History Page	16
Sales, Solutions, and Legal Information	
Worldwide Sales and Design Support	
Products	
PSoC® Solutions	17
Cypress Developer Community	17
Technical Support	



Product Portfolio

		V _a - Pange (V)			Power Dissipation					
Product	Range	V _{CC} Range (V) Min Typ ^[1] Max		Operating	l, I _{CC} (mA)	Standby,	I _{SB2} (μΑ)			
				Typ ^[1]	Max	Typ ^[1]	Max			
CY62256VNLL	Commercial	2.7	3.0	3.6	11	30	0.1	5		
CY62256VNLL	Industrial	2.7	3.0	3.6	11	30	0.1	10		
CY62256VNLL	Automotive-A	2.7	3.0	3.6	11	30	0.1	10		
CY62256VNLL	Automotive-E	2.7	3.0	3.6	11	30	0.1	130		

Pin Configurations

Figure 1. 28-pin SOIC and 28-pin TSOP I pinouts

Narrow SOIC Top View 8 1 A12 9 1 A13 10 1 1 1/O₂ 12 1 1/O₂ 13 1 1/O₂ 14 1 GND 15 1 1/O₃ 14 1 GND 15 1 1/O₃ 17 1 1/O₄ 19 1 1/O₅ 19 1 1/O₅ 19 1 1/O₅ 28 <u>VCC</u> A5 🗌 ¹0 ²² 23 7 21 OE 1 22 A1 224 A3 44 WE D 1 26 VCC 4 A3 44 WE D 1 28 VCC 4 A6 0 1 4 A7 0 1 4 A6 0 1 4 A7 0 1 4 A_0 A₆ [A₇ [27 🗌 WE 2 20 6 3 26 🛛 A4 5 A8 🗆 4 3 4 25 🛛 A3 $1/O_{6}$ $17 | I/O_{5}$ $16 | I/O_{4}$ $15 | I/O_{3}$ 14 | GND $13 | I/O_{2}$ 24 A2 23 A1 Ag 🛛 5 TSOP I TSOP I 2 A1006 **Reverse Pinout Top View**) 1 28 27 26 25 24 23 22 🗌 OE A11 7 **Top View** (not to scale) 21 🛛 A₀ A12 8 (not to scale) A13 [9 A14 [10 I/O₀ [11 I/O₁ [12 I/O₂ [13 20] CE 19 | 1/07 18 | 1/06 A₁₄ A₁₃ A₁₂ 22 0 21 A 17 1/05 16 I/O4 15 I/O3 GND C 14

Pin Definitions

Pin Number	Туре	Description
1–10, 21, 23–26	Input	A ₀ -A ₁₄ . Address inputs
11–13, 15–19	Input/Output	I/O ₀ -I/O ₇ . Data lines. Used as input or output lines depending on operation.
27	Input/Control	WE. When selected LOW, a WRITE is conducted. When selected HIGH, a READ is conducted.
20	Input/Control	CE. When LOW, selects the chip. When HIGH, deselects the chip.
22	Input/Control	OE . Output Enable. Controls the direction of the I/O pins. When LOW, the I/O pins behave as outputs. When deasserted HIGH, I/O pins are tristated, and act as input data pins.
14	Ground	GND. Ground for the device
28	Power Supply	V _{CC} . Power supply for the device

Note

1. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC}$ Typ, $T_A = 25$ °C, and $t_{AA} = 70$ ns.



Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.

Storage temperature65 °C to +150 °C
Ambient temperature with power applied55 °C to +125 °C
Supply voltage to ground potential (pin 28 to pin 14)0.5 V to +4.6 V
DC voltage applied to outputs in high Z State $^{[2]}$ 0.5 V to V_{CC} + 0.5 V
DC input voltage $^{[2]}$ 0.5 V to V_{CC} + 0.5 V
Output current into outputs (LOW)20 mA

Static discharge voltage	
(per MIL-STD-883, method 3015)	> 2001 V
Latch-up current	

Operating Range

Device	Range	Ambient Temperature (T _A) ^[3]	V _{CC}
CY62256VN	Commercial	0 °C to +70 °C	2.7 V to
	Industrial	–40 °C to +85 °C	3.6 V
	Automotive-A	–40 °C to +85 °C	
	Automotive-E	–40 °C to +125 °C	

Electrical Characteristics

Over the Operating Range

Deremeter	Description	Test Cand	ltione		-70		L lus ! t		
Parameter	Description	Test Cond	Test Conditions		Test Conditions		Тур [4]	Max	Unit
V _{OH}	Output HIGH voltage	I _{OH} = -1.0 mA	$V_{CC} = 2.7 V$	2.4	-	-	V		
V _{OL}	Output LOW voltage	I _{OL} = 2.1 mA	$V_{CC} = 2.7 V$	_	-	0.4	V		
V _{IH}	Input HIGH voltage			2.2	-	V _{CC} + 0.3	V		
V _{IL}	Input LOW voltage			-0.5	-	0.8	V		
I _{IX} Input lea	Input leakage current	$GND \le V_{IN} \le V_{CC}$	Commercial/ Industrial/ Automotive-A	-1	_	+1	μΑ		
			Automotive-E	-10	-	+10	μΑ		
I _{OZ}	Output leakage current	$\begin{array}{l} GND \leq V_{IN} \leq V_{CC}, \\ Output \ Disabled \end{array}$	Commercial/ Industrial/ Automotive-A	-1	_	+1	μΑ		
			Automotive-E	-10	_	+10	μA		
Icc	V _{CC} operating supply current	$V_{CC} = 3.6 \text{ V},$ $I_{OUT} = 0 \text{ mA},$ $f = f_{MAX} = 1/t_{RC}$	All ranges	-	11	30	mA		
I _{SB1}	Automatic CE power-down current - TTL inputs	$\label{eq:constraint} \begin{array}{l} \frac{V_{CC}}{CE} = 3.6 \text{ V},\\ \overline{CE} \geq V_{IH},\\ V_{IN} \geq V_{IH} \text{ or }\\ V_{IN} \leq V_{IL},\\ f = f_{MAX} \end{array}$	All ranges	-	100	300	μΑ		
I _{SB2}	Automatic CE power-down	$\frac{V_{CC}}{V_{CC}} = 3.6 \text{ V},$	Commercial	_	0.1	5	μΑ		
	current - CMOS inputs	$\label{eq:constraint} \begin{array}{l} \overline{\text{CE}} \geq \text{V}_{\text{CC}} - 0.3 \text{ V}, \\ \text{V}_{\text{IN}} \geq \text{V}_{\text{CC}} - 0.3 \text{ V} \text{ or} \\ \text{V}_{\text{IN}} \leq 0.3 \text{ V}, \text{ f} = 0 \end{array}$	Industrial/ Automotive-A	-		10			
			Automotive-E	_		130			

V_{IL}(min) = -2.0 V for pulse durations of less than 20 ns.
 T_A is the "Instant-On" case temperature.
 Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC} Typ, T_A = 25 °C, and t_{AA} = 70 ns.



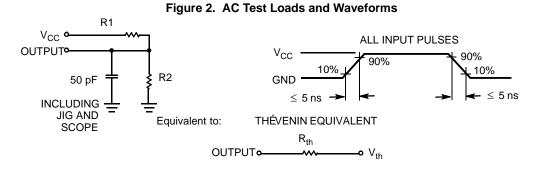
Capacitance

Parameter ^[5]	Description	Test Conditions	Max	Unit
C _{IN}	Input capacitance	$T_A = 25 \text{ °C}, f = 1 \text{ MHz}, V_{CC} = 3.0 \text{ V}$	6	pF
C _{OUT}	Output capacitance		8	pF

Thermal Resistance

Parameter ^[5]	Description	Test Conditions	SOIC	TSOPI	RTSOPI	Unit
θ_{JA}	(junction to ambient)	Still air, soldered on a 3 × 4.5 inch, two-layer	68.45	87.62	87.62	°C/W
θ ^{JC}	Thermal resistance (junction to case)	printed circuit board	26.94	23.73	23.73	°C/W

AC Test Loads and Waveforms



Parameter	Value	Units
R1	1100	Ohms
R2	1500	Ohms
RTH	645	Ohms
VTH	1.750	Volts

Note

5. Tested initially and after any design or process changes that may affect these parameters.



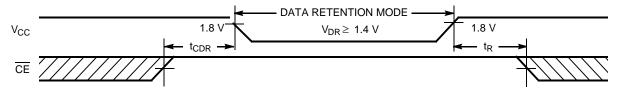
Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions ^[6]		Min	Тур [7]	Max	Unit
V _{DR}	V _{CC} for data retention			1.4	-	_	V
I _{CCDR}	Data retention current	$\frac{V_{CC}}{V_{CC}} = 1.4 \text{ V},$	Commercial	_	0.1	3	μΑ
		$\label{eq:constraint} \begin{array}{l} \frac{V_{CC}}{CE} = 1.4 \text{ V},\\ CE \geq V_{CC} - 0.3 \text{ V},\\ V_{IN} \geq V_{CC} - 0.3 \text{ V}\\ \text{or } V_{IN} \leq 0.3 \text{ V} \end{array}$	Industrial/ Automotive-A	_		6	
		01 VIN ≤ 0.5 V	Automotive-E	-		50	
t _{CDR} ^[6]	Chip deselect to data retention time			0	-	_	ns
t _R ^[8]	Operation recovery time			70	_	1	ns

Data Retention Waveform

Figure 3. Data Retention Waveform



- 6. No input may exceed V_{CC} + 0.3 V. 7. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC}$ Typ, $T_A = 25$ °C, and $t_{AA} = 70$ ns. 8. Tested initially and after any design or process changes that may affect these parameters.



Switching Characteristics

Over the Operating Range

Parameter ^[9]	Description	CY622	CY62256VN-70	
Parameter	Description		Max	- Unit
Read Cycle				•
t _{RC}	Read cycle time	70	-	ns
t _{AA}	Address to data valid	-	70	ns
t _{OHA}	Data hold from address change	10	-	ns
t _{ACE}	CE LOW to data valid	-	70	ns
t _{DOE}	OE LOW to data valid	-	35	ns
t _{LZOE}	OE LOW to low Z ^[10]	5	-	ns
t _{HZOE}	OE HIGH to high Z ^[10, 11]	-	25	ns
t _{LZCE}	CE LOW to low Z ^[10]	10	_	ns
t _{HZCE}	CE HIGH to high Z ^[10, 11]	-	25	ns
t _{PU}	CE LOW to power-up	0	-	ns
t _{PD}	CE HIGH to power-down	-	70	ns
Write Cycle [12	, 13]			
t _{WC}	Write cycle time	70	-	ns
t _{SCE}	CE LOW to write end	60	_	ns
t _{AW}	Address setup to write end	60	_	ns
t _{HA}	Address hold from write end	0	_	ns
t _{SA}	Address setup to write start	0	_	ns
t _{PWE}	WE pulse width	50	_	ns
t _{SD}	Data setup to write end	30	_	ns
t _{HD}	Data hold from write end	0	-	ns
t _{HZWE}	WE LOW to high Z ^[10, 11]	-	25	ns
t _{LZWE}	WE HIGH to low Z ^[10]	10	-	ns

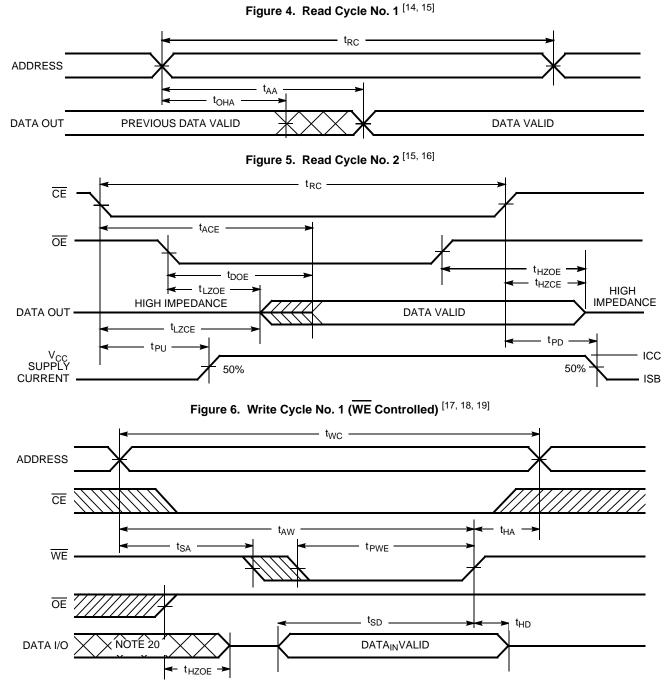
Notes

Test conditions assume signal transition time of 5 ns or less timing reference levels of V_{CC}/2, input pulse levels of 0 to V_{CC}, and output loading of the specified I_{OL}/I_{OH} and 100-pF load capacitance.

10. At any temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any device.
11. t_{HZOE}, t_{HZCE}, and t_{HZWE} are specified with C_L = 5 pF as in (b) of <u>AC</u> Test Loads. Transition is measured ± 200 mV from steady-state voltage.
12. The internal write time of the memory is defined by the overlap of <u>CE</u> LOW and <u>WE</u> LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and <u>hold</u> timing should be referenced to the rising edge of the signal that terminates the write.
13. The minimum write cycle time for write cycle #3 (WE controlled, OE LOW) is the sum of t_{HZWE} and t_{SD}.



Switching Waveforms



- Notes

 14. Device is continuously selected. OE, CE = V_{IL}.
 15. WE is HIGH for read cycle.
 16. Address valid prior to or coincident with CE transition LOW.
 17. The internal write time of the memory is defined by the overlap of CE LOW and WE LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
 18. Data I/O is high impedance if OE = V_{IL}.
 19. If CE goes HIGH simultaneously with WE HIGH, the output remains in a high impedance state.
 20. During this period, the I/Os are in output state and input signals should not be applied.

- 20. During this period, the I/Os are in output state and input signals should not be applied.



Switching Waveforms (continued)

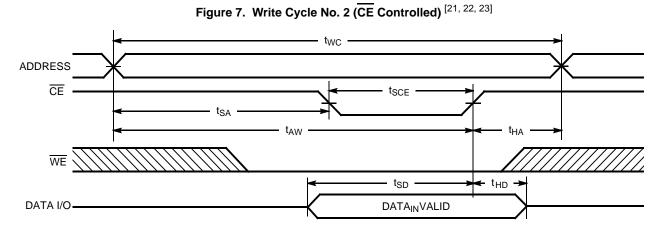
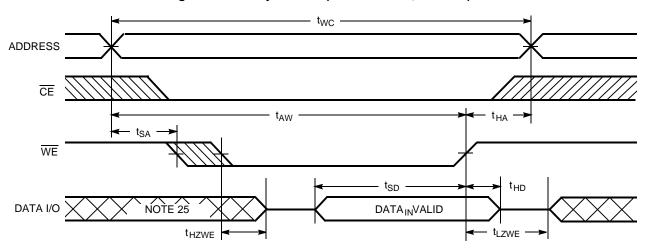


Figure 8. Write Cycle No. 3 (WE Controlled, OE LOW) ^[23, 24]



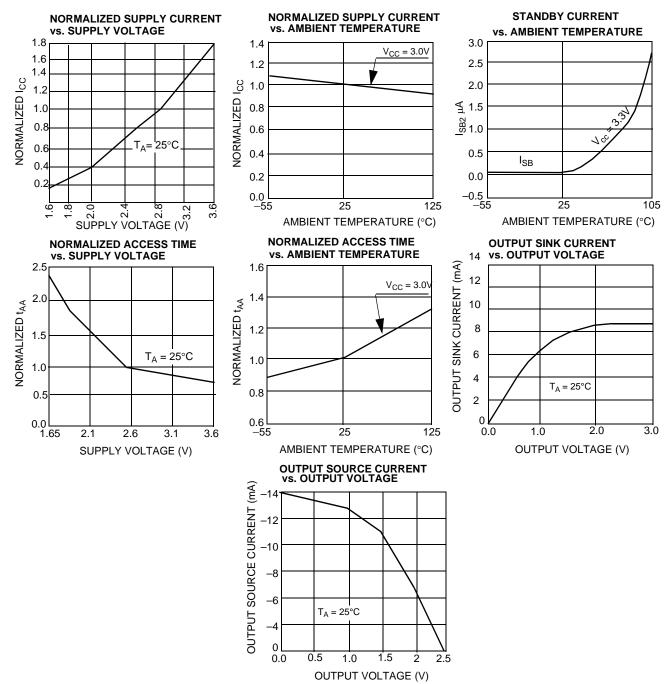
- 21. The internal write time of the memory is defined by the overlap of \overline{CE} LOW and \overline{WE} LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.

- 22. Data I/O is high impedance if $\overline{OE} = V_{IH}$. 23. If CE goes HIGH simultaneously with WE HIGH, the output remains in a high impedance state. 24. The minimum write cycle time for write cycle #3 (WE controlled, \overline{OE} LOW) is the sum of t_{HZWE} and t_{SD}. 25. During this period, the I/Os are in output state and input signals should not be applied.



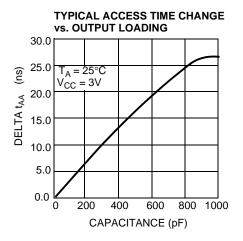


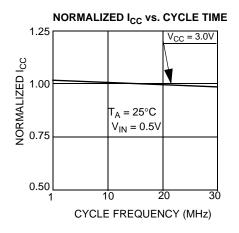
Typical DC and AC Characteristics





Typical DC and AC Characteristics (continued)





Truth Table

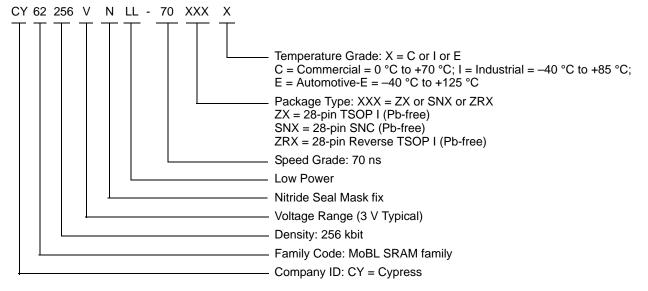
CE	WE	OE	Inputs/Outputs	Mode	Power
Н	Х	Х	High Z	Deselect/power-down	Standby (I _{SB})
L	Н	L	Data out	Read	Active (I _{CC})
L	L	Х	Data in	Write	Active (I _{CC})
L	Н	Н	High Z	Deselect, output disabled	Active (I _{CC})



Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
70	CY62256VNLL-70ZXC	51-85071	28-pin TSOP I (Pb-free)	Commercial
	CY62256VNLL-70SNXI	51-85092	28-pin SNC (300 Mils) Narrow Body (Pb-free)	Industrial
	CY62256VNLL-70ZXI	51-85071	28-pin TSOP I (Pb-free)	
	CY62256VNLL-70ZRXI	51-85074	28-pin Reverse TSOP I (Pb-free)	
	CY62256VNLL-70SNXE	51-85092	28-pin SNC (300 Mils) Narrow Body (Pb-free)	Automotive-E
	CY62256VNLL-70ZXE	51-85071	28-pin TSOP I (Pb-free)	

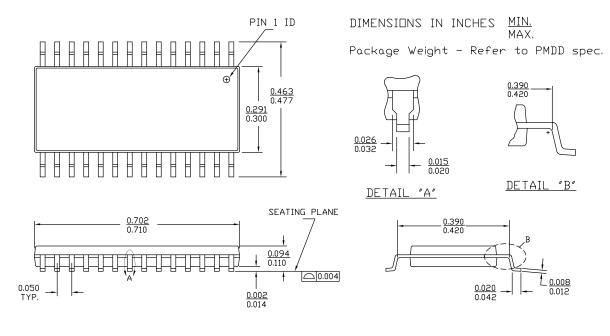
Ordering Code Definitions



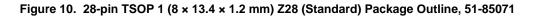


Package Diagrams

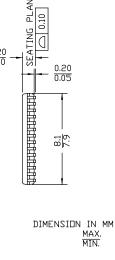
Figure 9. 28-pin SNC (300 Mils) SN28.3 (Narrow Body) Package Outline, 51-85092



51-85092 *E



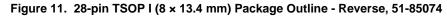
DRIENTATION I.D MAY BE LOCATED EITHER NDTE: SEATING PLANE AS SHOWN IN OPTION 1 OR OPTION 2 0.10 13.6 13.2 0 1.20 1.00 11.9 11.7 OPTION 1 (SEE NOTE) 0.55 BSC. Ò OPTION 2 (SEE NOTE) <u>7.9</u> 0.27 0.18 Ł <u>0.20</u> 0.12 <u>1.02</u> 0.91 ر ا 0°-5° $\frac{0.7}{0.3}$ 0.25 GAUGE PLANE

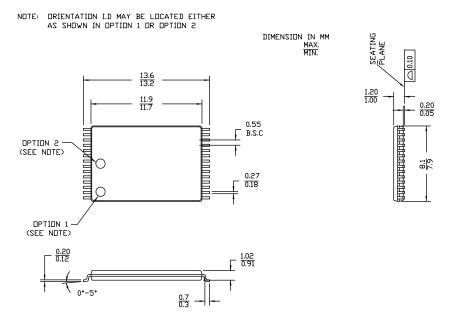


51-85071 *I



Package Diagrams





51-85074 *G



Acronyms

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
I/O	Input/Output
SRAM	Static Random Access Memory
TSOP	Thin Small Outline Package
VFBGA	Very Fine-Pitch Ball Grid Array

Document Conventions

Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
μΑ	microampere
mA	milliampere
MHz	megahertz
ns	nanosecond
Ω	ohm
pF	picofarad
V	volt
W	watt





Document History Page

Document Title: CY62256VN, 256-Kbit (32 K × 8) Static RAM Document Number: 001-06512				
Revision	ECN	Orig. of Change	Submission Date	Description of Change
**	426504	NXR	See ECN	New data sheet
*A	488954	NXR	See ECN	Added Automotive product Updated ordering Information table
*В	2769239	VKN/AESA	09/25/09	Corrected VIL description in the Electrical Characteristics table
*C	2901521	AJU	03/30/2010	Removed inactive parts from Ordering Information. Updated Package Diagram.
*D	3119519	AJU	01/04/2011	Updated Ordering Information. Added Ordering Code Definitions.
*E	3329873	RAME	07/27/11	Updated template and styles according to current Cypress standards. Added acronyms and units. Removed reference to AN1064 SRAM system guidelines. Updated operation recovery time parameter under Data Retention Characteristics on page 6.
*F	4122787	VINI	09/13/2013	Updated Package Diagrams: spec 51-85092 – Changed revision from *C to *E.
				Updated in new template.
				Completing Sunset Review.



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